

INVESTIGATION OF POTENTIAL INDUCED DEGRADATION ON THE REAR SIDE OF BIFACIAL PERC+ SOLAR CELLS

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INTRODUCTION AND MOTIVATION

- PERC+ cell concept [1] successfully introduced to mass production
- bifacial gain facilitates reduced LCOE
- absence of full cover rear side metallization: potential of solar cells no longer shielded versus grounded frame or glass on rear side [2]

➔ Is rear side of bifacial PERC cells prone to PID ?

EXPERIMENTAL

Samples and testing conditions

- three types industrially produced PERC+ cells in test
- batches **A, B, C**, two cells per batch
- 20 cm x 20 cm one cell modules built from each cell type
- material stack: 3 mm glass / EVA / cell / EVA / 3 mm glass
- module stressed under $U_{PID} = +1000$ V applied to brass plate, cell at ground level
- test duration = 24 h to 96 h, cell temperature 60°C
- dark IV curve measured in 5 min interval during degradation using source meter

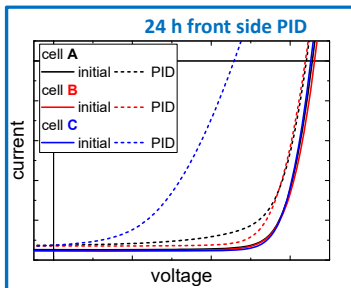


- time, temperature voltage according to SEMI PV75-1016

➔ PID sensitivity tested for front and rear side

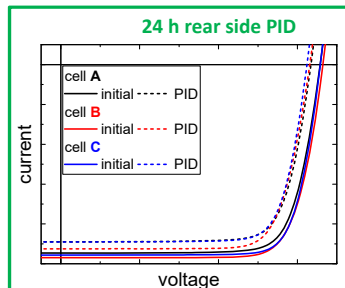
OVERVIEW: DEGRADATION IN CELL PARAMETERS

Illuminated I-V characteristics – on LED solar simulator (STC)



PID-s for front side under test

- $\Delta I_{sc} = -2.4\%$ (-2.5%, -3%)
- $\Delta V_{oc} = -2.3\%$ (-3.5%, -29.8%)
- $\Delta FF = -9\%$ (-1.9%_{rel}, -39.8%_{rel})
- main impact on FF for **A** and **C** typical for PID-s [3]



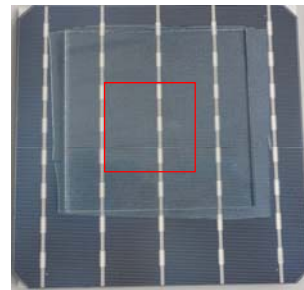
PID-p for rear side under test

- $\Delta I_{sc} = -5.9\%$ (-4.6%, -6.9%)
- $\Delta V_{oc} = -3.5\%$ (-5.0%, -5.1%)
- FF not affected

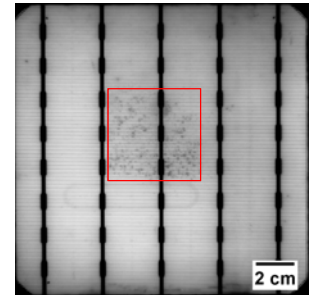
➔ all cells in test are prone to degradation from the rear side, so called PID-p causes passivation failure

LATERAL INHOMOGENEOUS PID-p DISTRIBUTION

- local PID test on PIDcon [4]



photograph of cell with rear side up: locally PID stressed at highlighted area

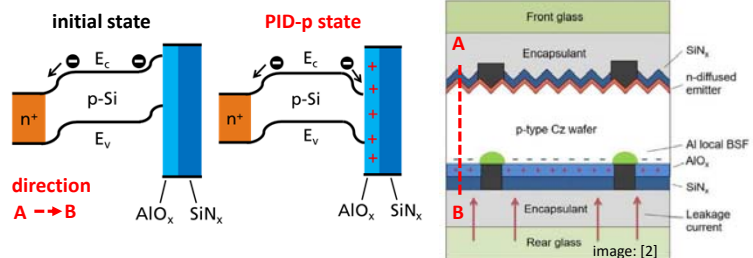


photoluminescence image after 96h PID stress at 1000V bias voltage, rear side up

Hypothesis:

- positive ions enrich in AlO_x layer, reducing field effect passivation [5]
- structural defects or stacking faults in Si or AlO_x facilitates PID-p [6]

PID-p BAND DIAGRAM MODEL



- rear side passivation by field effect of negative charges in AlO_x layer
- initial state:** electrons repelled from fixed negative charges in AlO_x
- PID-p state:** positive ions, e.g. Sodium, overcompensate AlO_x layer [6]

➔ break down of field effect passivation can explain PID-p

SUMMARY

- PERC+ cells in glass/glass module suffer from PID at rear side
- PID-p type reduced open circuit voltage and current, rather than fill factor
- lateral inhomogeneous degradation: structural defects facilitate PID-p
- presumably PID-p relates to local breakdown of field effect passivation of AlO_x layer caused by in-diffusion of positive ions

REFERENCES

- [1] Dullweber, T., et al.; Progress in Photovoltaics: Research and Applications 24.12 (2016): 1487-1498
- [2] Luo, W., et al.; Progress in Photovoltaics: Research and Applications (2018).
- [3] Nagel, H. et al.; 26th EUPVSEC. 2011. S. 3107-3112.
- [4] www.pidcon.com
- [5] To be shown in forthcoming publication
- [6] Naumann, V., et al.; Solar Energy Materials and Solar Cells 120 (2014): 383-389.